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### PJN1NA60 / PJW1NA60 / PJU1NA60 / PJD1NA60

Current

1 A

#### **600V N-Channel MOSFET**

600 V

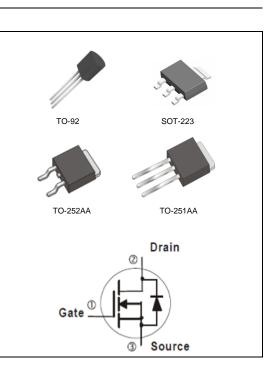
Voltage

#### Features

- R<sub>DS(ON)</sub>, V<sub>GS</sub>@10V,I<sub>D</sub>@0.5A<14Ω
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

- Case : TO-251AA, TO-252AA, SOT-223, TO-92 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- TO-251AA Approx. Weight : 0.0104 ounces, 0.297grams
- TO-252AA Approx. Weight : 0.0104 ounces, 0.297grams
- SOT-223 Approx. Weight : 0.043 ounces, 0.123grams
- TO-92 Approx. Weight : 0.007 ounces, 0.196grams



### **Maximum Ratings and Thermal Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER		SYMBOL	TO-251AA	TO-252AA	SOT-223	TO-92	UNITS
Drain-Source Voltage		V <sub>DS</sub>	600				V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 30				V
Continuous Drain Current		I <sub>D</sub>	1 0.3		.3	А	
Pulsed Drain Current		I <sub>DM</sub>	4 1.2		.2	А	
Single Pulse Avalanche Energy (Note 1)		E <sub>AS</sub>	50				mJ
Power Dissipation	T <sub>c</sub> =25°C	P <sub>D</sub>	2	7	3.3	3	W
	Derate above 25°C		0.2	216	0.026	0.024	W/°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150			°C	
Typical Thermal resistance							
- Junction to Case		$R_{ extsf{ heta}JC}$	4.	63	-	-	°C/W
- Junction to Ambient		$R_{ extsf{ heta}JA}$	1 <sup>.</sup>	10	37.9 <sup>(Note 4)</sup>	140	

• Limited only By Maximum Junction Temperature





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#### **Electrical Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =250uA	600	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250$ uA	2	3.34	4	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V,I <sub>D</sub> =0.5A	-	11.1	14	Ω
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =600V,V <sub>GS</sub> =0V	-	0.02	1.0	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 30V,V <sub>DS</sub> =0V	-	<u>+</u> 10	<u>+</u> 100	nA
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A,V <sub>GS</sub> =0V	-	0.85	1.4	V
Dynamic (Note 5)						
Total Gate Charge	Qg		-	3.3	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =480V, I <sub>D</sub> =1A, V <sub>GS</sub> =10V <sup>(Note 2,3)</sup>	-	1.1	-	
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	1	-	
Input Capacitance	Ciss		-	95	-	pF
Output Capacitance	Coss	$V_{DS}=25V, V_{GS}=0V,$	-	21	-	
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	0.3	-	
Turn-On Delay Time	td <sub>(on)</sub>	(on)		5	-	
Turn-On Rise Time	t <sub>r</sub>	$V_{DD}=300V, I_{D}=1A,$ $R_{G}=25\Omega^{(Note 2,3)}$	-	20	-	ns
Turn-Off Delay Time	td <sub>(off)</sub>	$R_{G}=25\Omega$	-	8	-	
Turn-Off Fall Time	t <sub>f</sub>		-	25	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			-	-	1	A
Diode Forward Current	I <sub>S</sub>					
Maximum Pulsed Drain-Source				-	4	А
Diode Forward Current	I <sub>SM</sub>		-			
Reverse Recovery Time	trr	V <sub>GS</sub> =0V, I <sub>S</sub> =1A	-	190	-	ns
Reverse Recovery Charge	Qrr	dI <sub>F</sub> / dt=100A/us <sup>(Note 2)</sup>	-	0.53	-	uC

NOTES :

1. L=30mH, I<sub>AS</sub>=1.77A, V<sub>DD</sub>=50V, R<sub>G</sub>=25 ohm, Starting T<sub>J</sub>=25  $^{\circ}$ C

2. Pulse width  $\leq$  300 us, Duty cycle  $\leq$  2%

3. Essentially independent of operating temperature typical characteristics.

4. ReJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper

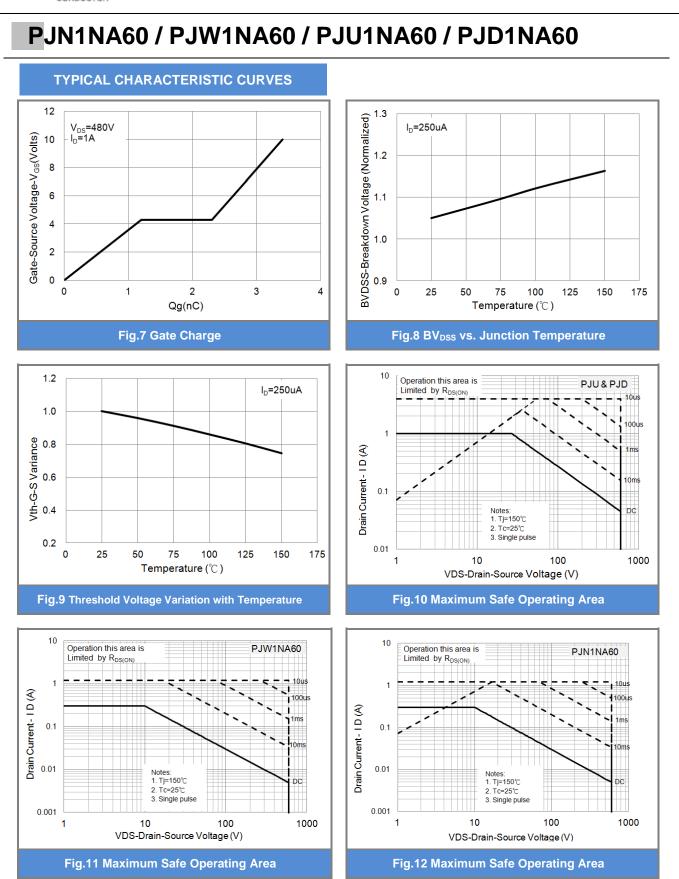
5. Guaranteed by design, not subject to production testing.





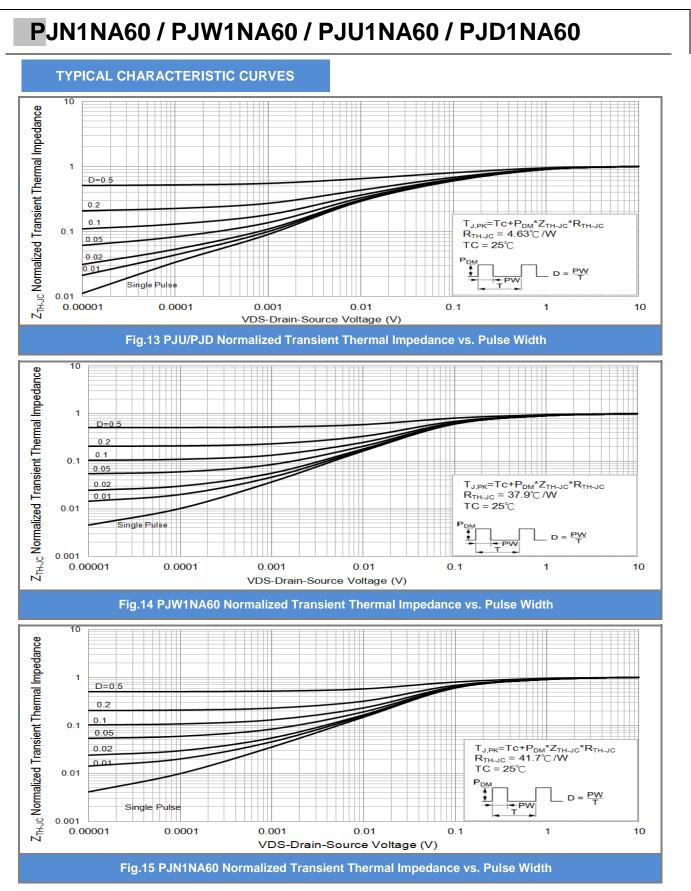
#### PJN1NA60 / PJW1NA60 / PJU1NA60 / PJD1NA60 **TYPICAL CHARACTERISTIC CURVES** 1.2 1.5 V<sub>DS</sub>=50V V<sub>GS</sub>=10V V<sub>GS</sub>=8V I<sub>Ds</sub>-Drain-to-Source Current(A) I<sub>DS</sub>-Drain-to-S ource Current(A) 1.2 0.9 0.6 V<sub>GS</sub>=5V 0.3 T\_=25 T\_=125℃ V<sub>GS</sub>=4.5V 0.0 0 10 20 30 40 50 0 2 6 8 10 4 VDS- Drain-to-Source Voltage(V) VGS-Gate-to-Source Voltage(V) **Fig.1 Output Characteristics Fig.2 Transfer Characteristics** 15 3.0 V<sub>GS</sub>= 10V V<sub>GS</sub>=10V, I<sub>D</sub>=0.5A R<sub>DS</sub>(on)- On-Resistance (Normalized) 14 2.5 $R_{DS}(on)$ - On-Resistance( $\Omega$ ) 13 2.0 1.5 12 1.0 11 10 0.5 9 0.0 0.0 0.2 0.4 0.6 0.8 1.0 0 25 50 75 100 125 150 175 Temperature (℃) IDS-Drain-to-Source Current(A) Fig.3 On-Resistance vs. Drain Current Fig.4 On-Resistance vs. Junction Temperature 1000 10 Ciss Is-Source to-Drain Current(A) 100 1 Capacitance (pF) Coss 0.1 10 0.01 1 T<sub>i</sub>=125℃ T<sub>i</sub>=25℃ Crss V<sub>GS</sub>=0V f=1MHz 0.001 0.1 0 0.3 0.6 0.9 1.2 1.5 0.1 10 100 1 VDS-Drain-Source Voltage (V) VSD-Source-to-Drain Voltage(V) Fig.5 Capacitance vs. Drain-Source Voltage Fig.6 Source-Drain Diode Forward Voltage







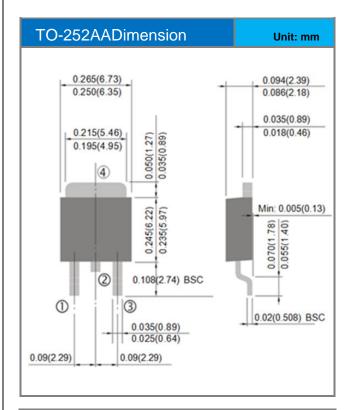


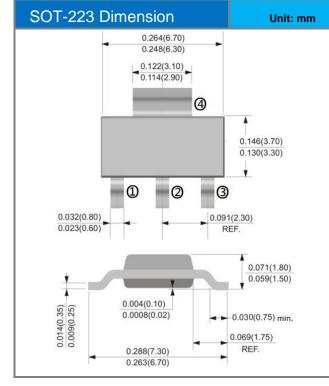


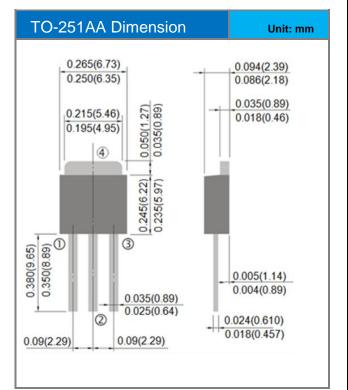


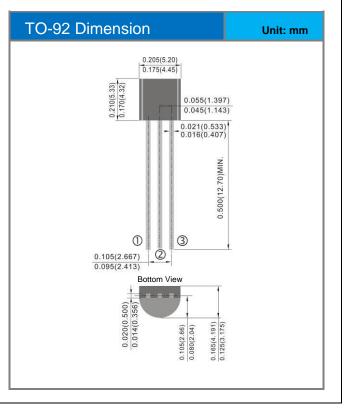


#### Packaging Information













# PJN1NA60 / PJW1NA60 / PJU1NA60 / PJD1NA60

#### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJU1NA60_T0_00001	TO-251AA	80pcs / Tube	U1NA60	Halogen free
PJD1NA60_L2_00001	TO-252AA	3,000pcs / 13" reel	D1NA60	Halogen free
PJW1NA60_R2_00001	SOT-223	2,500pcs / 13" reel	1NA60	Halogen free
PJN1NA60_B0_00001	TO-92	1000pcs / bag	1NA60	Halogen free
PJN1NA60_A0_00001	TO-92 AMMO	2000pcs / box	1NA60	Halogen free





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